

## RQJ0305EQDQS

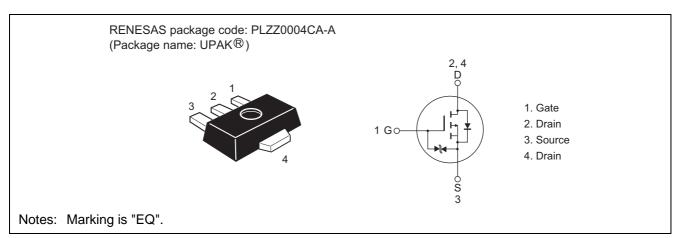
# Silicon P Channel MOS FET Power Switching

REJ03G1779-0100 Rev.1.00 Mar 16, 2009

### **Features**

- Low gate drive
  - $V_{DSS}$ : -30 V and 2.5 V gate drive
- Low drive current
- High speed switching
- Small traditional power package (UPAK)

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

		( /	
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	-30	V
Gate to source voltage	$V_{GSS}$	+8 / -12	V
Drain current	I <sub>D</sub>	-3.4	Α
Drain peak current	I <sub>D(pulse)</sub> Note1	-12	А
Body - drain diode reverse drain current	I <sub>DR</sub>	3.4	А
Channel dissipation	Pch Note2	1.5	W
Thermal resistance	Rth(ch-a) Note2	83	°C /W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \le 10 \mu s$ , Duty cycle  $\le 1\%$ 

2. When using the glass epoxy board (FR-4  $40\times40\times1$  mm)

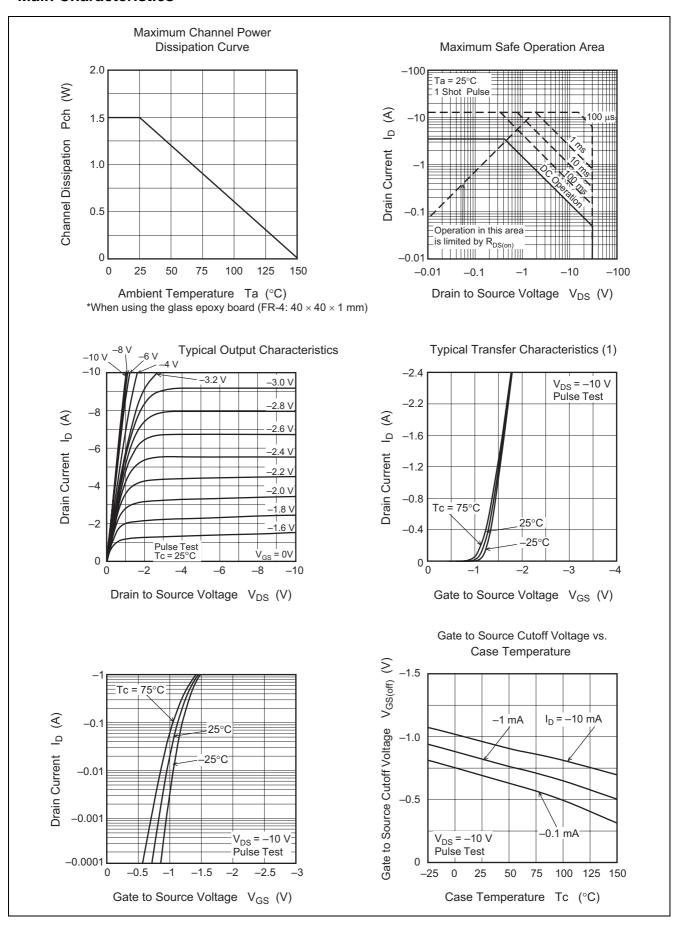
### **Electrical Characteristics**

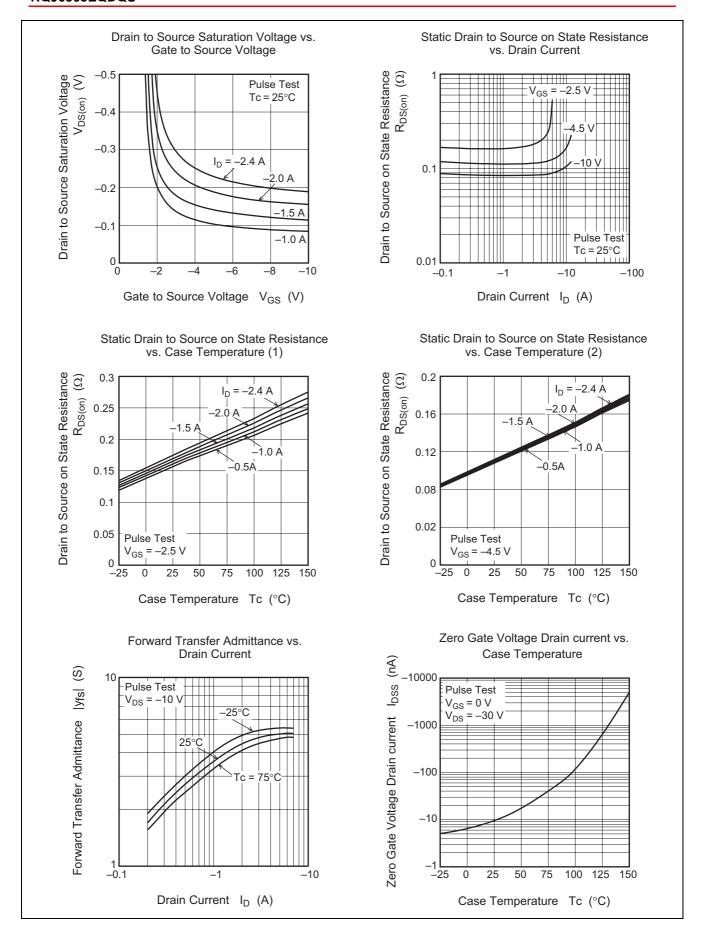
 $(Ta = 25^{\circ}C)$ 

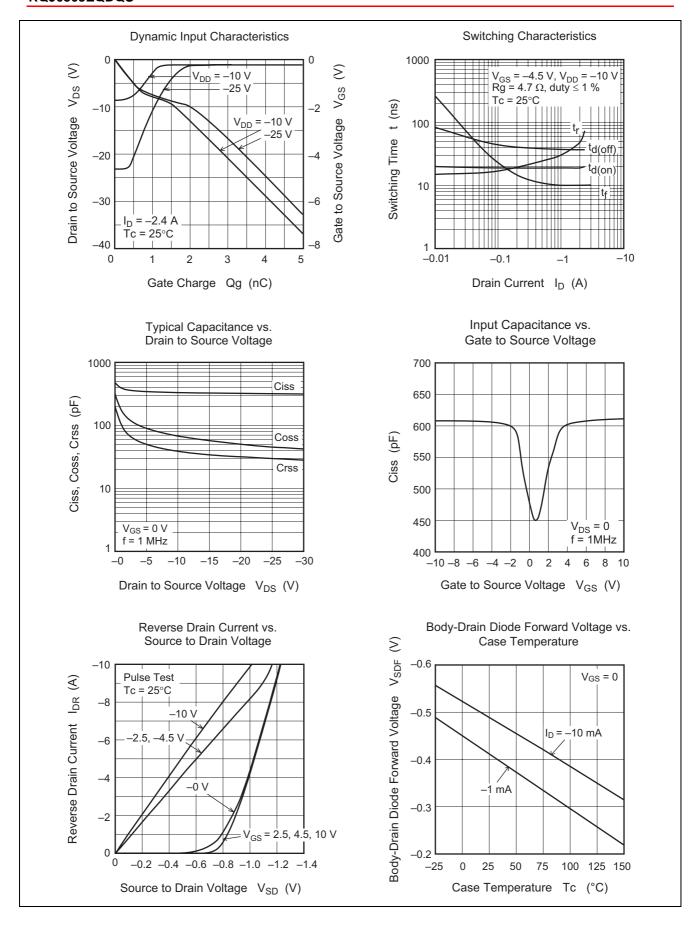
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	_	_	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	+8	_	_	V	$I_G = +100 \mu\text{A},  V_{DS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	-12	_	_	V	$I_G = -100 \mu\text{A},  V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	+10	μΑ	$V_{GS} = +6 \text{ V}, V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	-10	μΑ	$V_{GS} = -10 \text{ V}, V_{DS} = 0$
Drain to source leak current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.4	_	-1.4	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Drain to source on state resistance	R <sub>DS(on)</sub>	_	110	140	mΩ	$I_D = -1.7 \text{ A}, V_{GS} = -4.5 \text{ V}^{\text{Note3}}$
Drain to source on state resistance	R <sub>DS(on)</sub>		165	230	mΩ	$I_D = -1.7 \text{ A}, V_{GS} = -2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y <sub>fs</sub>	3.0	4.3	_	S	$I_D = -1.7 \text{ A}, V_{DS} = -10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	330	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	70	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	40	_	pF	
Turn - on delay time	t <sub>d(on)</sub>	_	17	_	ns	$I_D = -1.3 \text{ A}$
Rise time	t <sub>r</sub>	_	37	_	ns	$V_{GS} = -4.5 \text{ V}$
Turn - off delay time	t <sub>d(off)</sub>	_	39	_	ns	$R_L = 7.7 \Omega$
Fall time	t <sub>f</sub>	_	10	_	ns	$R_g = 4.7 \Omega$
Total gate charge	Qg	_	3.0	_	nC	V <sub>DD</sub> = -10 V
Gate to Source charge	Qgs	_	0.6	_	nC	$V_{GS} = -4.5 \text{ V}$
Gate to drain charge	Qgd	_	1.3	_	nC	$I_D = -2.4 \text{ A}$
Body - drain diode forward voltage	$V_{DF}$	_	-0.9	-1.3	V	$I_F = -3.4 \text{ A}, V_{GS} = 0^{\text{Note3}}$

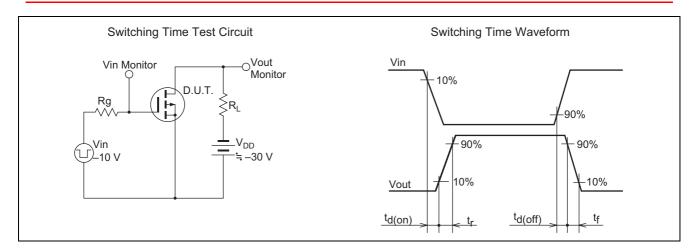
Notes: 3. Pulse test

### **Main Characteristics**

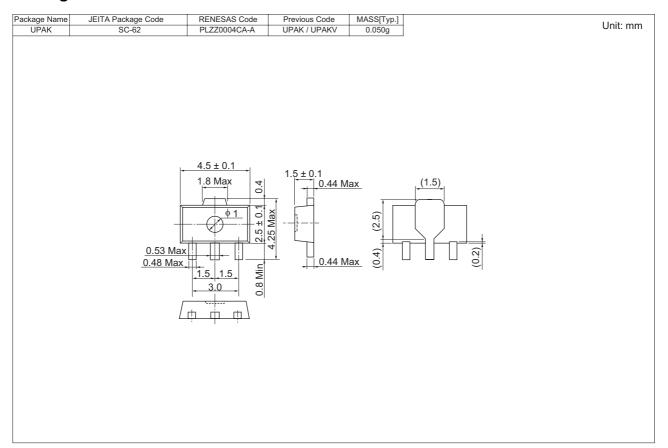








### **Package Dimensions**



### **Ordering Information**

Part No.	Quantity	Shipping Container
RQJ0305EQDQSTL-E	1000 pcs.	φ178 mm reel, 12 mm Emboss taping

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